

2SA1585

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into two groups, Q and R, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



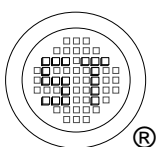
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	20	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	2	A
Peak Collector Current ($P_W = 10\text{ ms}$)	$-I_{CP}$	5	A
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 100\text{ mA}$	Current Gain Group Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
Collector Base Cutoff Current at $-V_{CB} = 20\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	20	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 0.1\text{ A}$	$-V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $-V_{CE} = 2\text{ V}$, $I_E = 500\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	240	-	MHz	
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	35	-	pF	



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ISO 9001:2008
Certificate No. 18073088



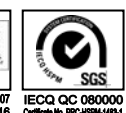
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ISO 9001:2008
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BS-ENAS 18001:2007
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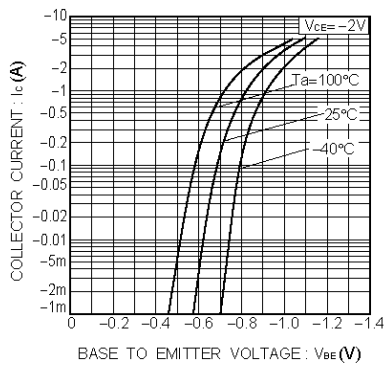


Fig. 1 Grounded emitter propagation characteristics

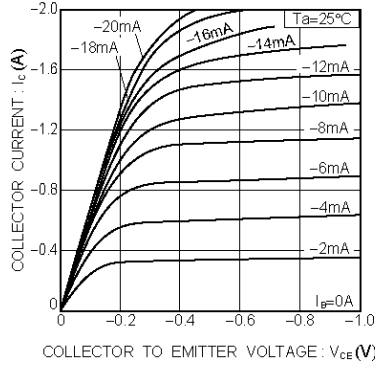


Fig. 2 Grounded emitter output characteristics (I)

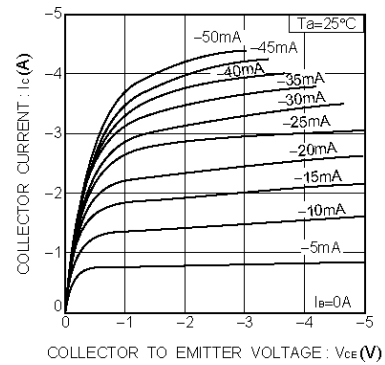


Fig. 3 Grounded emitter output characteristics (II)

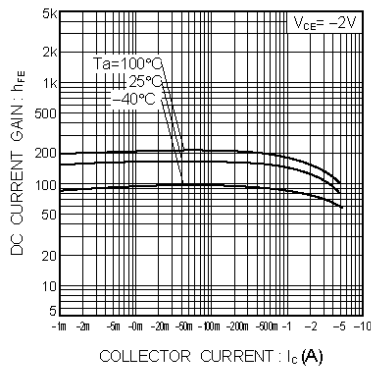


Fig. 4 DC current gain vs. collector current

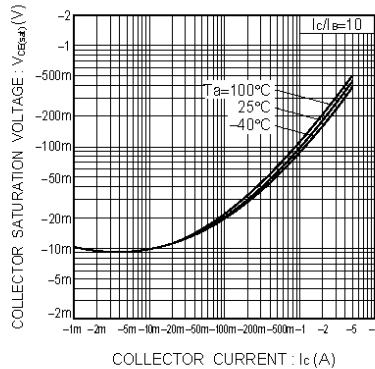


Fig. 5 Collector-emitter saturation voltage vs. collector current (I)

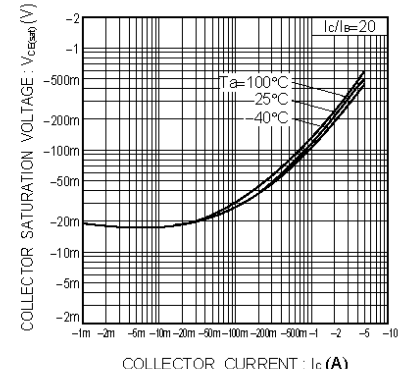


Fig. 6 Collector-emitter saturation voltage vs. collector current (II)

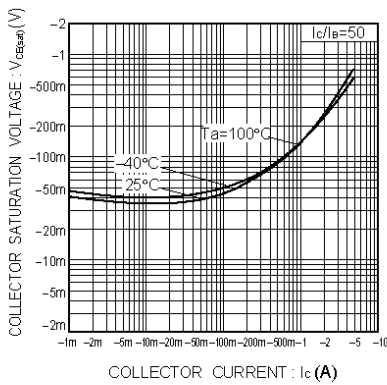


Fig. 7 Collector-emitter saturation voltage vs. collector current (III)

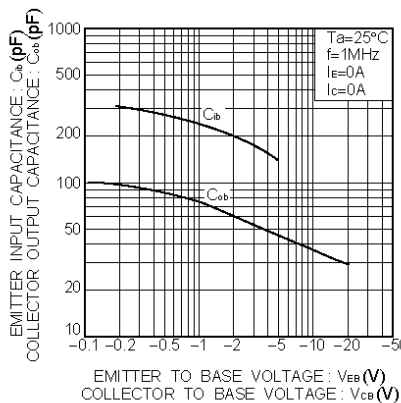


Fig. 8 Gain bandwidth product vs. emitter current
Collector output capacitance vs. collector-base voltage

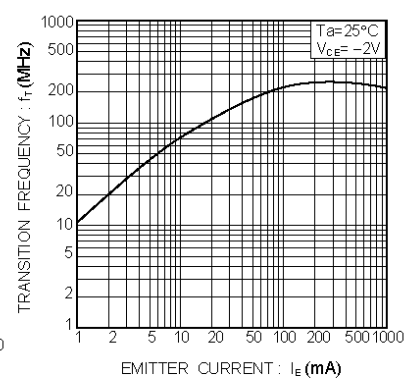


Fig. 9 Emitter input capacitance vs. emitter base voltage

